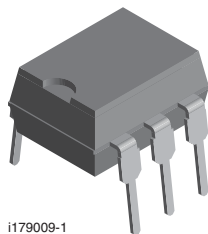
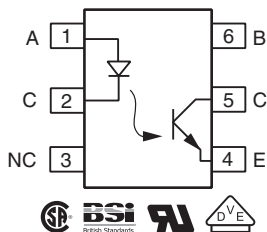




Optocoupler, Phototransistor Output, no Base Connection



i179009-1



FEATURES

- Isolation test voltage, 5300 V_{RMS}
- No base terminal connection for improved common mode interface immunity
- Long term stability
- Industry standard dual in line package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

The MOC8101, MOC8102, MOC8103, MOC8104, MOC8105 family optocoupler consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon planar phototransistor detector in a plastic plug-in DIP-6 package.

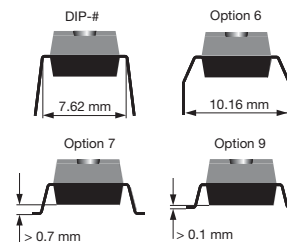
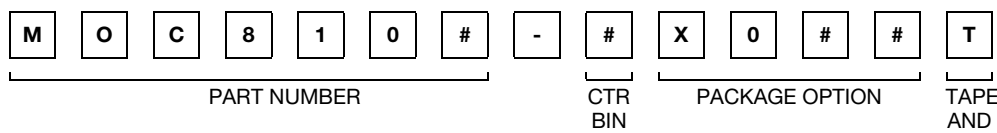
The coupling device is suitable for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

The base terminal of the MOC8101, MOC8102, MOC8103, MOC8104, MOC8105 is not connected, resulting in a substantially improved common mode interference immunity.

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)				
	10 mA				
UL, CSA, BSI	50 to 80	73 to 117	108 to 173	160 to 256	65 to 133
DIP-6	MOC8101	MOC8102	MOC8103	MOC8104	MOC8105
DIP-6, 400 mil, option 6	-	MOC8102-X006	-	-	-
SMD-6, option 9	MOC8101-X009	MOC8102-X009	-	-	-
VDE, UL, CSA, BSI	50 to 80	73 to 117	108 to 173	160 to 256	65 to 133
DIP-6	MOC8101-X001	-	MOC8103-X001	-	-
DIP-6, 400 mil	-	MOC8102-X016	-	MOC8104-X016	-
SMD-6, option 7	MOC8101-X017T	MOC8102-X017T	-	-	-
SMD-6, option 9	-	-	-	MOC8104-X019T	-

Note

- Additional options may be possible, please contact sales office.



ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	6.0	V
Forward continuous current		I _F	60	mA
Surge forward current	t ≤ 10 μs	I _{FSM}	2.5	A
Power dissipation		P _{diss}	100	mW
Derate linearly from 25°C			1.33	mW/°C
OUTPUT				
Collector emitter breakdown voltage		BV _{CEO}	30	V
Emitter collector breakdown voltage		BV _{ECO}	7.0	V
Collector current		I _C	50	mA
Derate linearly from 25°C			2.0	mW/°C
Power dissipation		P _{diss}	150	mW
COUPLER				
Isolation test voltage		V _{ISO}	5300	V _{RMS}
Creepage distance			≥ 7.0	mm
			8.0 ⁽²⁾	mm
Clearance distance			≥ 7.0	mm
			8.0 ⁽²⁾	mm
Isolation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175	
Isolation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²	Ω
Derate linearly from 25 °C			3.33	mW/°C
Total power dissipation		P _{tot}	250	mW
Storage temperature		T _{stg}	- 55 to + 150	°C
Operating temperature		T _{amb}	- 55 to + 100	°C
Junction temperature		T _j	100	°C
Soldering temperature ⁽¹⁾	max. 10 s, dip soldering; distance to seating plane ≥ 1.5 mm	T _{slid}	260	°C

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).
- (2) Applies to wide bending option 6.

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I _F = 10 mA		V _F		1.25	1.5	V
Breakdown voltage	I _R = 10 μA		V _{BR}	6.0			V
Reverse current	V _R = 6.0 V		I _R		0.01	10	μA
Capacitance	V _R = 0 V, f = 1.0 MHz		C _O		25		pF
Thermal resistance			R _{thja}		750		K/W
OUTPUT							
Collector emitter capacitance	V _{CE} = 5.0 V, f = 1.0 MHz		C _{CE}		5.2		pF
Collector emitter dark current	V _{CE} = 10 V, T _{amb} = 25 °C	MOC8101	I _{CEO1}		1.0	50	nA
	V _{CE} = 10 V, T _{amb} = 100 °C	MOC8102	I _{CEO1}		1.0		μA
Collector emitter breakdown voltage	I _C = 1.0 mA		BV _{CEO}	30			V
Emitter collector breakdown voltage	I _E = 100 μA		BV _{ECO}	7.0			V
Thermal resistance			R _{thja}		500		K/W
COUPLER							
Saturation voltage collector emitter	I _F = 5.0 mA		V _{CEsat}		0.25	0.4	V
Coupling capacitance			C _C		0.6		pF

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



CURRENT TRANSFER RATIO ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$V_{CE} = 10\text{ V}$, $I_F = 10\text{ mA}$	MOC8101	CTR	50		80	%
		MOC8102	CTR	73		117	%
		MOC8103	CTR	108		173	%
		MOC8104	CTR	160		256	%
		MOC8105	CTR	65		133	%

SWITCHING CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Turn-on time	$V_{CC} = 10\text{ V}$, $I_C = 2.0\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{on}		3.0		μs
Turn-off time	$V_{CC} = 10\text{ V}$, $I_C = 2.0\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{off}		2.3		μs
Rise time	$V_{CC} = 10\text{ V}$, $I_C = 2.0\text{ mA}$, $R_L = 100\text{ }\Omega$	t_r		2.0		μs
Fall time	$V_{CC} = 10\text{ V}$, $I_C = 2.0\text{ mA}$, $R_L = 100\text{ }\Omega$	t_f		2.0		μs
Cut off frequency		f_{co}		250		kHz

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

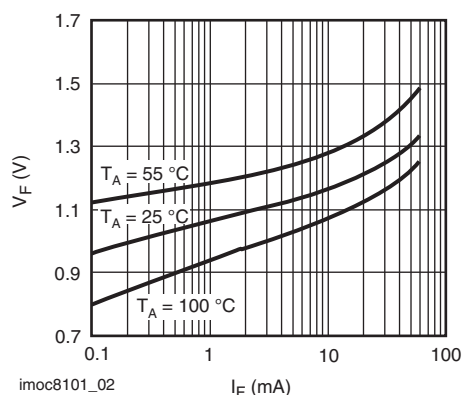


Fig. 1 - Forward Voltage vs. Forward Current

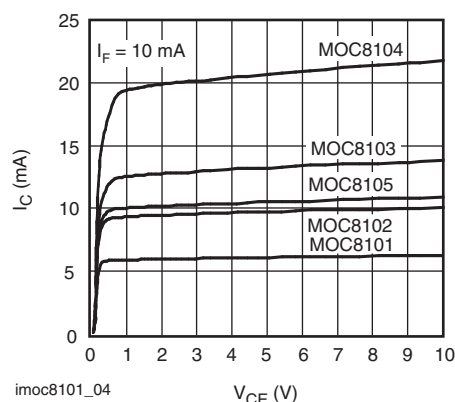


Fig. 3 - Collector Current vs. Collector Emitter Voltage

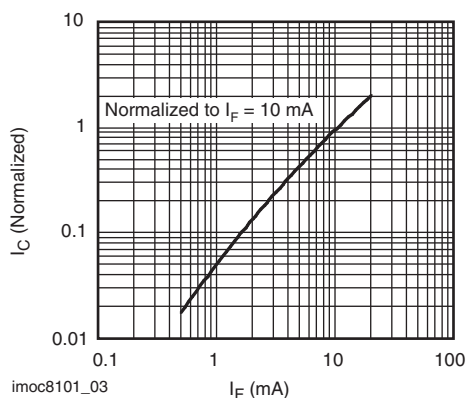


Fig. 2 - Collector Current vs. LED Forward Current

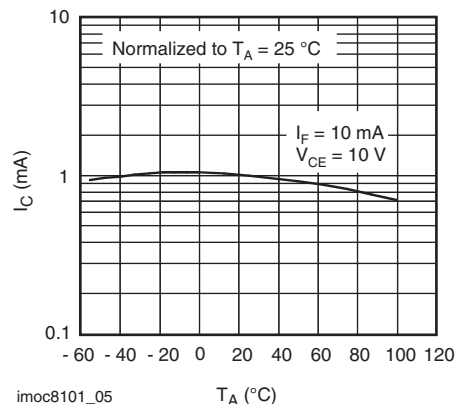


Fig. 4 - Collector Current vs. Ambient Temperature

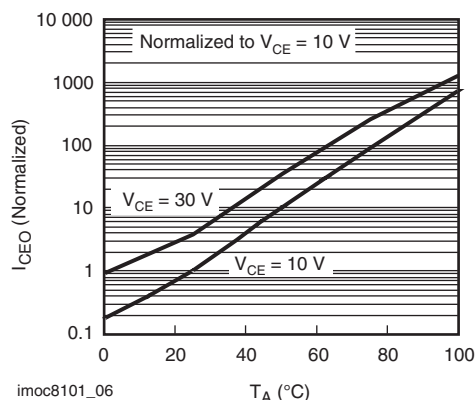


Fig. 5 - Collector Emitter Dark Current vs. Ambient Temperature

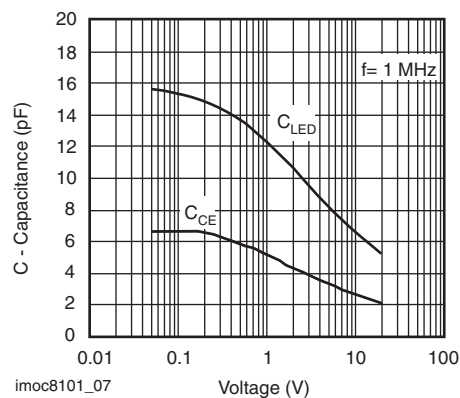


Fig. 6 - Capacitance vs. Voltage

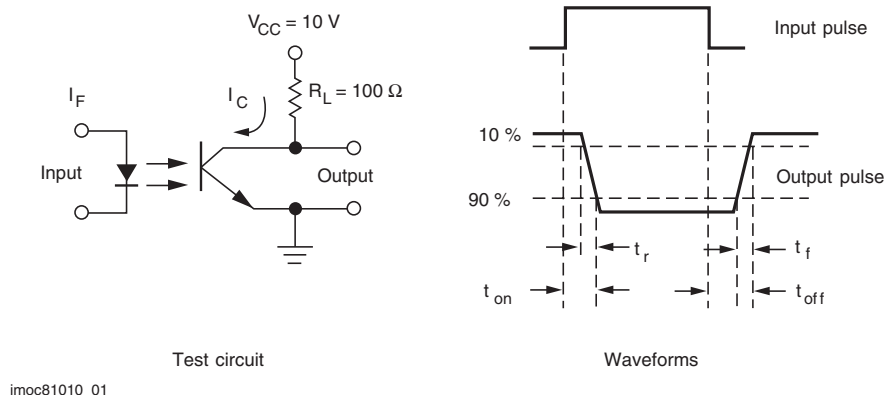
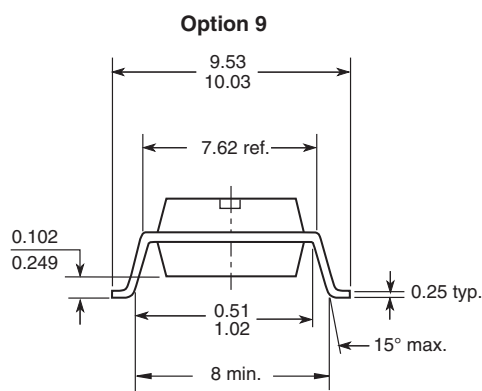
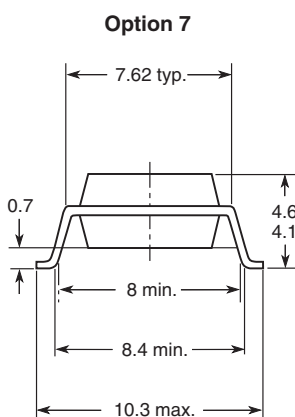
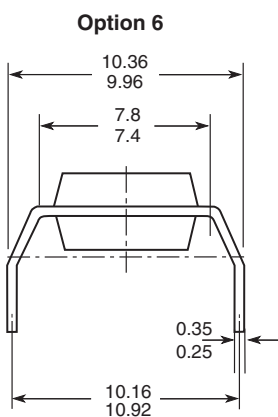
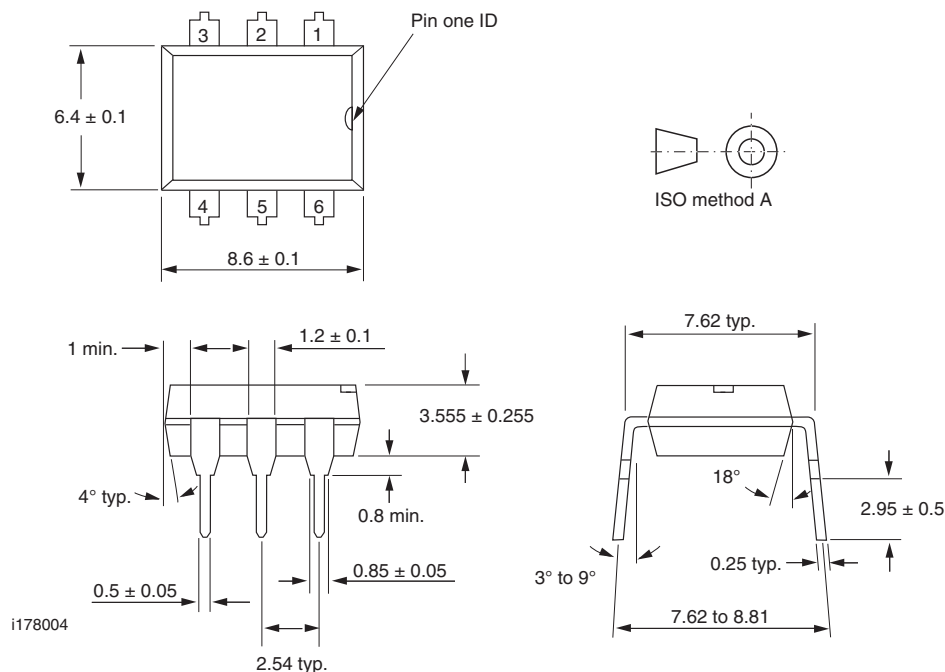


Fig. 7 - Switching Time Test Circuit and Waveforms



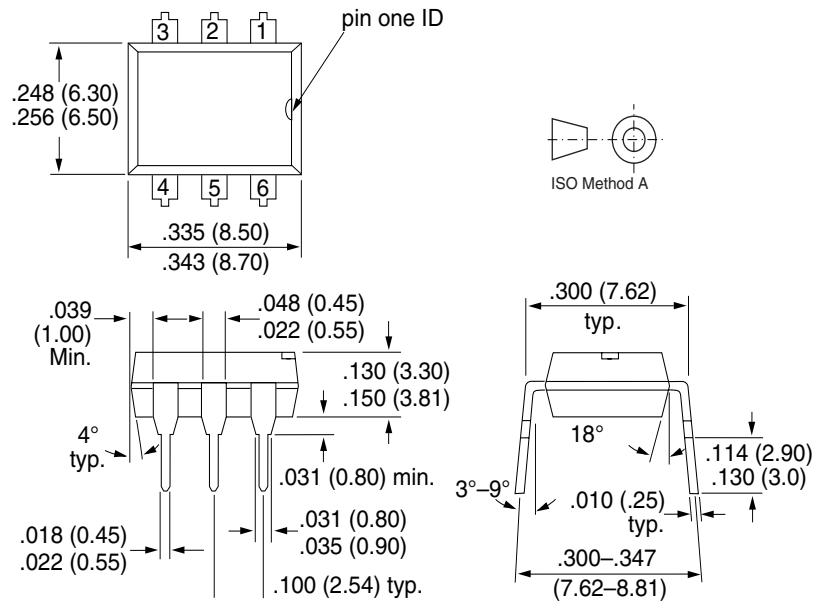
PACKAGE DIMENSIONS in millimeters



18450

DIP-6A

Package Dimensions in Inches (mm)



i178004

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

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Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423



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